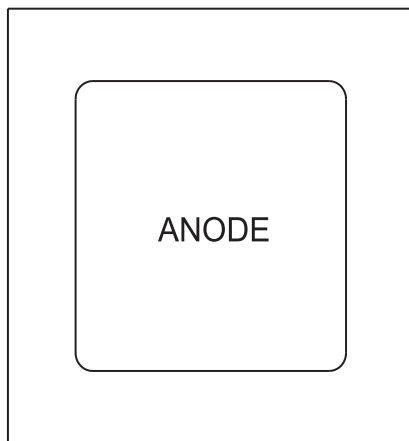


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	18 X 18 MILS
Die Thickness	7.5 MILS
Anode Bonding Pad Area	11 X 11 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 14,000Å

GEOMETRY



BACKSIDE CATHODE R0

GROSS DIE PER 4 INCH WAFER

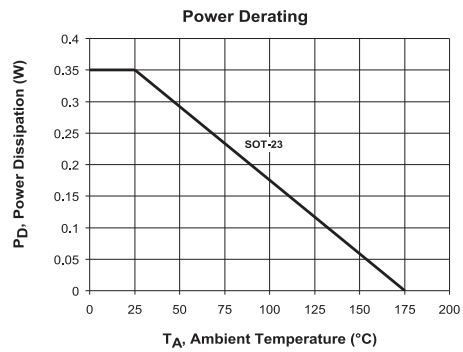
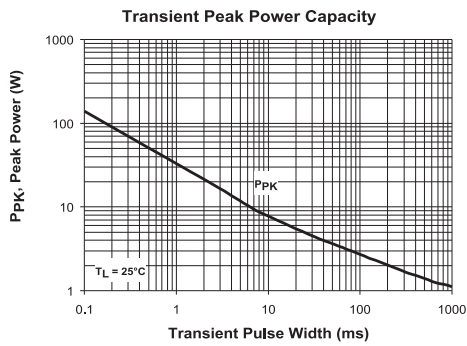
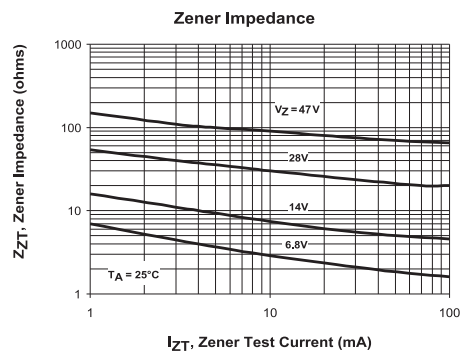
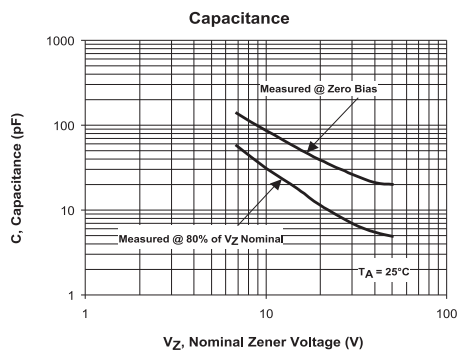
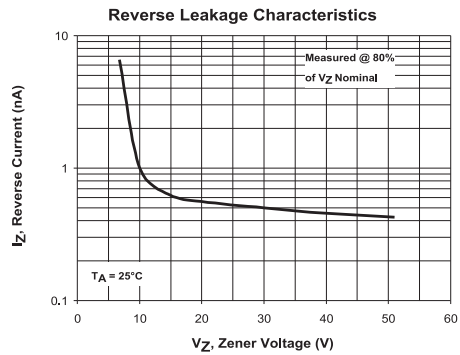
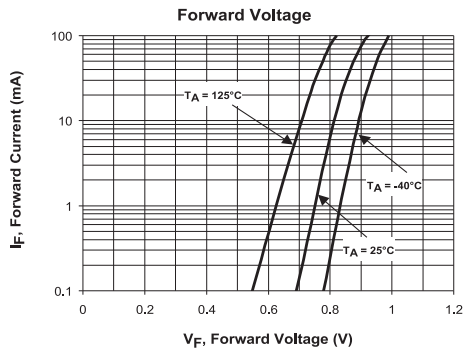
36,600

PRINCIPAL DEVICE TYPES

CMPZ5235B
THRU
CMPZ5261B

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R2 (1-August 2002)



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